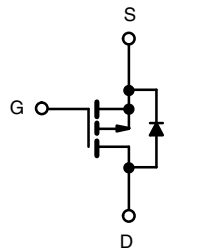


P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 60
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.0135
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.017
I_D (A)	- 50
Configuration	Single



P-Channel MOSFET

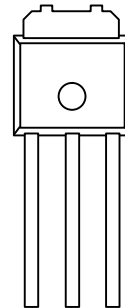
FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested



RoHS
COMPLIANT
HALOGEN
FREE

TO-251



Drain Connected to
Drain-Tab

G D S
Top View

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	I_D	$T_C = 25$ °C - 50	A
		$T_C = 125$ °C - 38	
Continuous Source Current (Diode Conduction) ^a	I_S	- 50	
Pulsed Drain Current ^b	I_{DM}	- 200	
Single Pulse Avalanche Current	I_{AS}	- 52	
Single Pulse Avalanche Energy	E_{AS}	135	mJ
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C 136	W
		$T_C = 125$ °C 45	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.1	

Notes

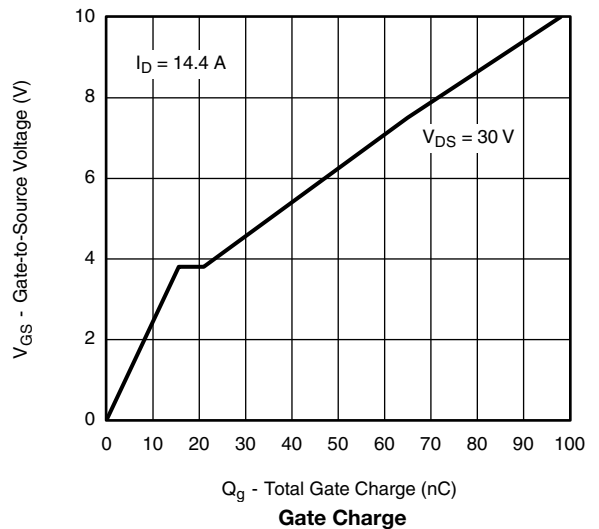
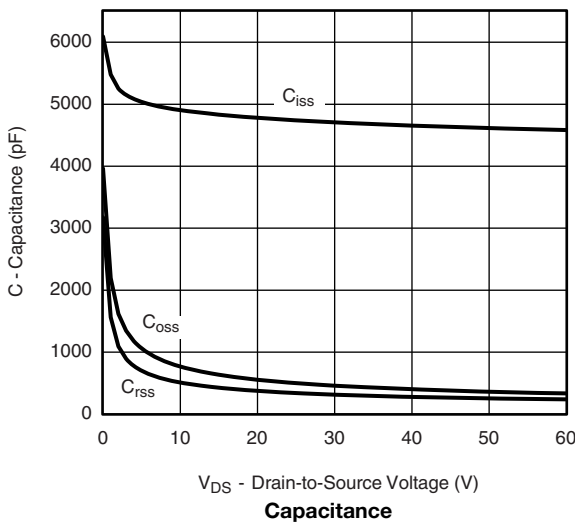
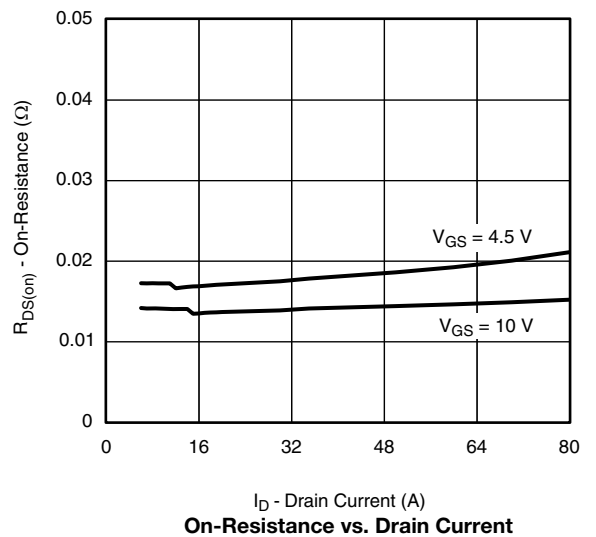
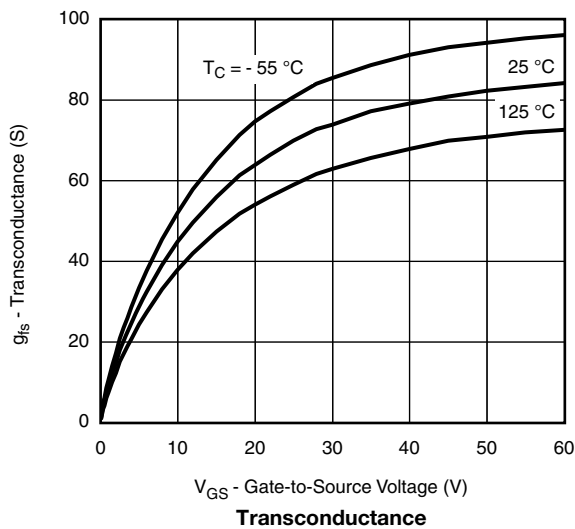
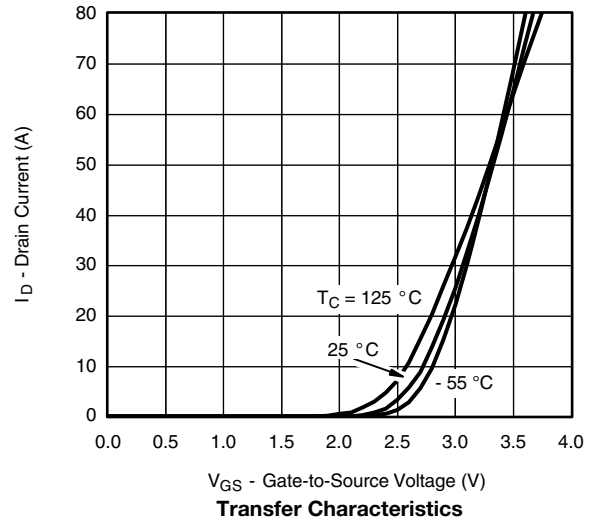
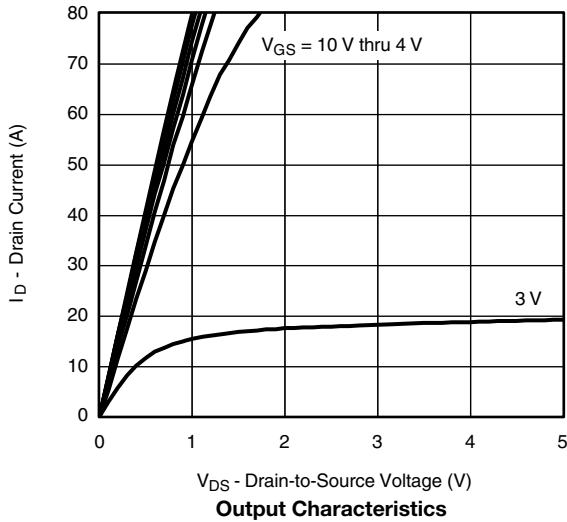
- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).

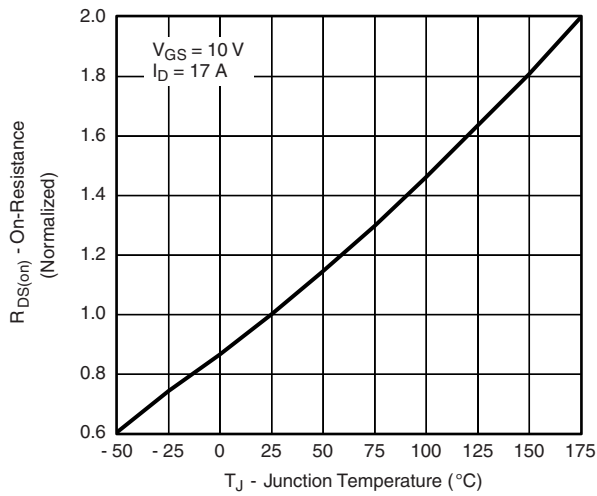
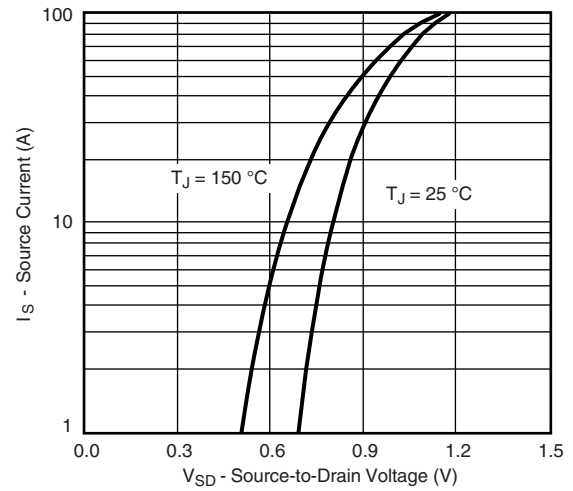
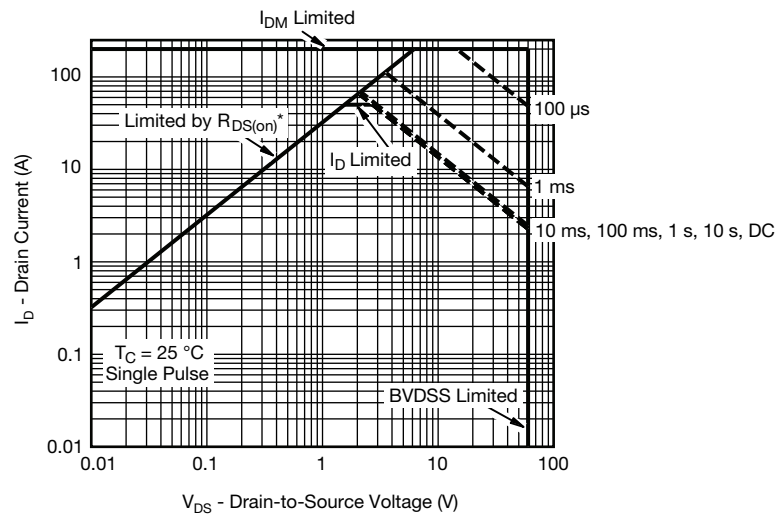
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA		- 60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA		- 1.5	-	- 2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 60 V	-	-	- 1	μA
		V _{GS} = 0 V	V _{DS} = - 60 V, T _J = 125 °C	-	-	- 50	
		V _{GS} = 0 V	V _{DS} = - 60 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≥ - 5 V	- 50	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 17 A	-	0.0135	-	Ω
		V _{GS} = - 10 V	I _D = - 50 A, T _J = 125 °C	-	0.026	-	
		V _{GS} = - 10 V	I _D = - 50 A, T _J = 175 °C	-	0.032	-	
		V _{GS} = - 4.5 V	I _D = - 14 A	-	0.017	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 17 A		-	50	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = - 25 V, f = 1 MHz	-	4730	5910	pF
Output Capacitance	C _{oss}			-	485	606	
Reverse Transfer Capacitance	C _{rss}			-	330	410	
Total Gate Charge ^c	Q _g	V _{GS} = - 10 V	V _{DS} = - 30 V, I _D = - 50 A	-	98	150	nC
Gate-Source Charge ^c	Q _{gs}			-	15	23	
Gate-Drain Charge ^c	Q _{gd}			-	21	32	
Gate Resistance	R _g	f = 1 MHz		1.47	2.9	4.42	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 30 V, R _L = 0.6 Ω I _D ≅ - 50 A, V _{GEN} = - 10 V, R _g = 6.0 Ω		-	15	18	ns
Rise Time ^c	t _r			-	12	16	
Turn-Off Delay Time ^c	t _{d(off)}			-	112	125	
Fall Time ^c	t _f			-	39	48	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	- 200	A
Forward Voltage	V _{SD}	I _F = - 50 A, V _{GS} = 0 V		-	- 0.8	- 1.5	V

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

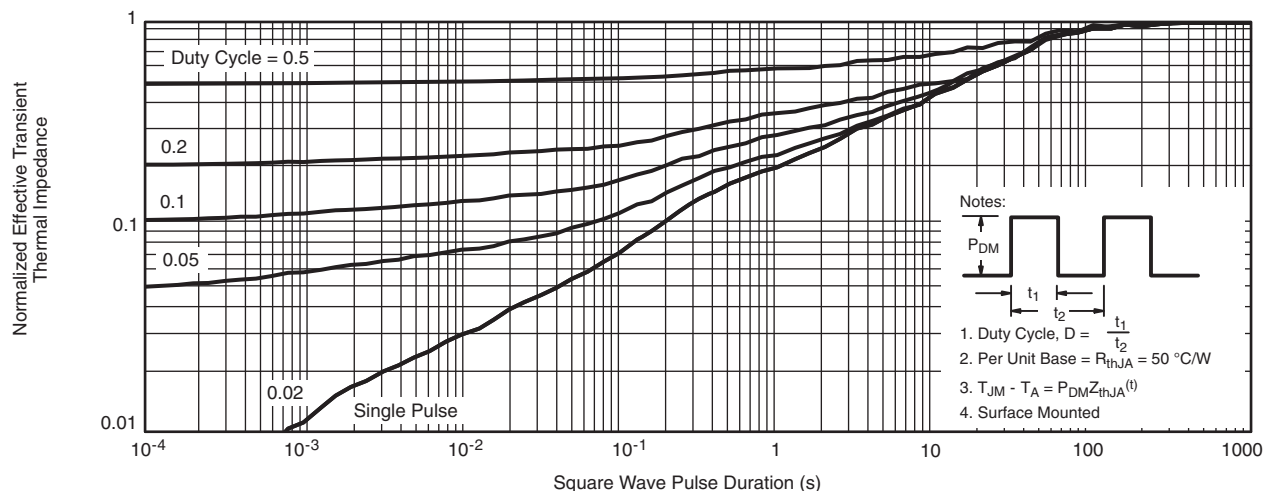
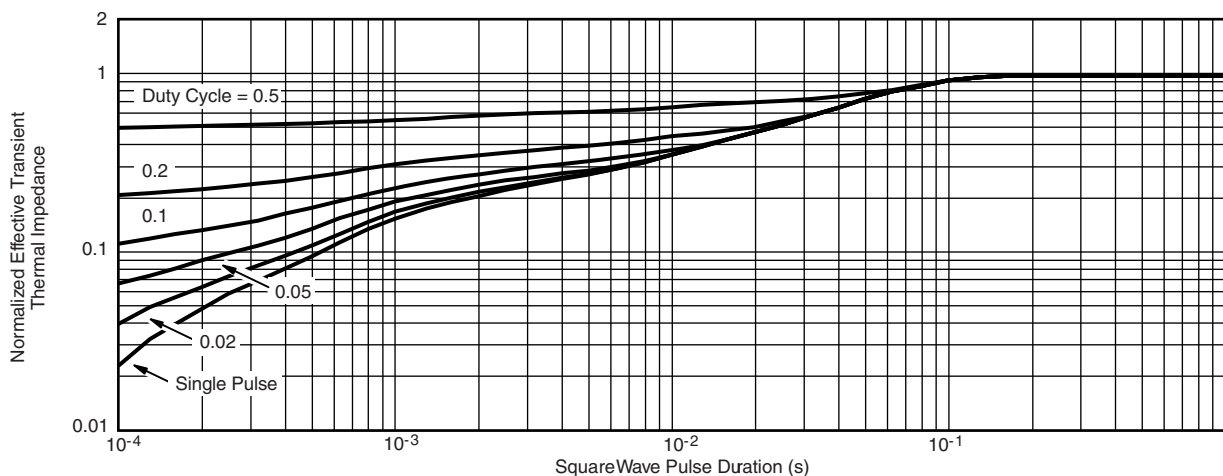
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


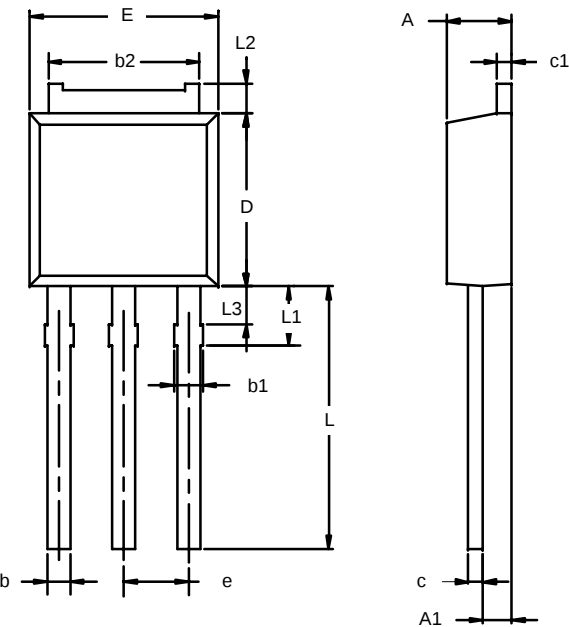
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-251AA



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	3.89	9.53	0.153	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060

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